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Patent
Attorney's Docket No. 015290-508

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)	
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Paul SHUFFLEBOTHAM et al.)	Group Art Unit: Unassigned
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Application No.: 09/775,664)	Examiner: Unassigned
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Filed: February 5, 2001)	
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For: INDUCTIVELY COUPLED)	
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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed, some of which are also available in parent Application No. 08/772,374 (now U.S. Patent No. 6,184,158). The search report for a related PCT application (PCT/US97/22987) and the documents cited therein are enclosed.

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U.S. Patent No. 4,579,618, Celestino et al., issued 04/01/86;
U.S. Patent No. 4,614,639, Hegedus, issued 09/30/86;
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The documents are being submitted within 3 months of the filing or entry of the national stage of this application or before the first Office Action on the merits, whichever is later, therefore no fee or certification is required under 37 C.F.R. § 1.97(b).

To assist the Examiner, the documents listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

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By: _____


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